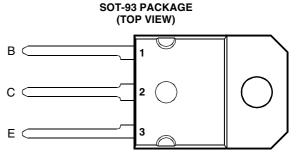
## BD546, BD546A, BD546B, BD546C PNP SILICON POWER TRANSISTORS

# BOURNS®

- Designed for Complementary Use with the BD545 Series
- 85 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BD546		-40		
Callester base valtage (I)	BD546A	M	-60	v	
Collector-base voltage ( $I_E = 0$ )	BD546B	V <sub>СВО</sub>	-80	v	
	BD546C		-100		
	BD546		-40		
Collector-emitter voltage ( $I_B = 0$ ) (see Note 1)	BD546A	V	-60	v	
	BD546B	CEO	-80	v	
	BD546C		-100	l	
Emitter-base voltage		V <sub>EBO</sub>	-5	V	
Continuous collector current		Ι <sub>C</sub>	-15	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2	P <sub>tot</sub>	85	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note	P <sub>tot</sub>	3.5	W		
Operating free air temperature range	T <sub>A</sub>	-65 to +150	°C		
Operating junction temperature range	Тj	-65 to +150	°C		
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C		
Lead temperature 3.2 mm from case for 10 seconds	ΤL	260	°C		

NOTES: 1. These values apply when the base-emitter diode is open circuited.

2. Derate linearly to 150°C case temperature at the rate of 0.68 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

#### PRODUCT INFORMATION

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## BD546, BD546A, BD546B, BD546C PNP SILICON POWER TRANSISTORS



#### electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITIONS			ТҮР	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage			BD546	-40			
		L _ 20 mA	1 – 0	BD546A	-60			v
		I <sub>C</sub> = -30 mA (see Note 4)	$I_{B} = 0$	BD546B	-80			v
		(see Note 4)		BD546C	-100			
		$V_{CE} = -40 V$	$V_{BE} = 0$	BD546			-0.4	
	Collector-emitter	V <sub>CE</sub> = -60 V	$V_{BE} = 0$	BD546A			-0.4	mA
ICES	cut-off current	V <sub>CE</sub> = -80 V	$V_{BE} = 0$	BD546B			-0.4	ma
		V <sub>CE</sub> = -100 V	$V_{BE} = 0$	BD546C			-0.4	
I <sub>CEO</sub>	Collector cut-off	V <sub>CE</sub> = -30 V	I <sub>B</sub> = 0	BD546/546A			-0.7	mA
	current	V <sub>CE</sub> = -60 V	I <sub>B</sub> = 0	BD546B/546C			-0.7	ШA
I <sub>EBO</sub>	Emitter cut-off	V <sub>EB</sub> = -5 V	I <sub>C</sub> = 0				-1	mA
EBO	current		Ū.					
	Forward current	$V_{CE} = -4 V$	I <sub>C</sub> = -1 A		60			
h <sub>FE</sub>	transfer ratio	$V_{CE} = -4 V$	I <sub>C</sub> = -5 A	(see Notes 4 and 5)	25			
		$V_{CE} = -4 V$	-		10			
V <sub>CE(sat)</sub>	Collector-emitter	I <sub>B</sub> = -625 mA	I <sub>C</sub> = -5 A	(see Notes 4 and 5)			-0.8	v
CE(sat)	saturation voltage	I <sub>B</sub> = -2 A	I <sub>C</sub> = -10 A				-1	ļ
$V_{BE}$	Base-emitter voltage	$V_{CE} = -4 V$	I <sub>C</sub> = -10 A	(see Notes 4 and 5)			-1.8	V
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -0.5 A	f = 1  k   z	20			
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -0.5 A	f = 1 MHz	3			

NOTES: 4. These parameters must be measured using pulse techniques,  $t_p = 300 \text{ } \mu s$ , duty cycle  $\leq 2\%$ .

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### thermal characteristics

PARAMETER	MIN	ТҮР	MAX	UNIT
R <sub>0JC</sub> Junction to case thermal resistance			1.47	°C/W
R <sub>0JA</sub> Junction to free air thermal resistance			35.7	°C/W

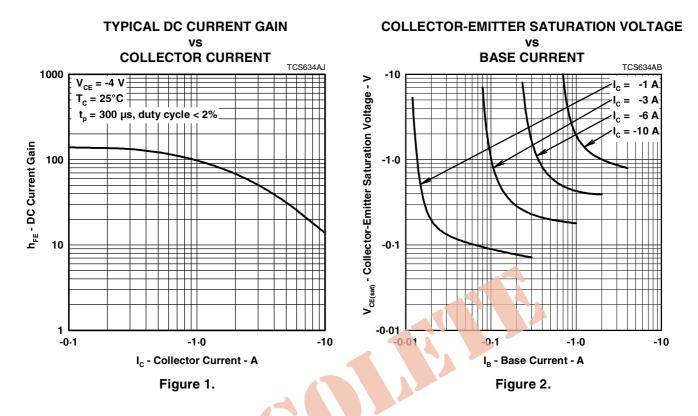
#### resistive-load-switching characteristics at 25°C case temperature

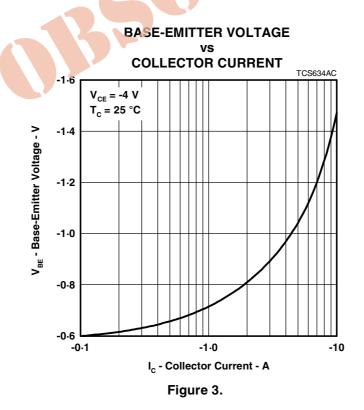
	PARAMETER	TEST CONDITIONS <sup>†</sup>			MIN	ТҮР	MAX	UNIT
t <sub>on</sub>	Turn-on time	I <sub>C</sub> = -6 A	I <sub>B(on)</sub> = -0.6 A	$I_{B(off)} = 0.6 A$		0.4		μs
t <sub>off</sub>	Turn-off time	$V_{BE(off)} = 4 V$	$R_L = 5 \Omega$	$t_p$ = 20 µs, dc $\leq$ 2%		0.7		μs

<sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

## BD546, BD546A, BD546B, BD546C PNP SILICON POWER TRANSISTORS

### **TYPICAL CHARACTERISTICS**



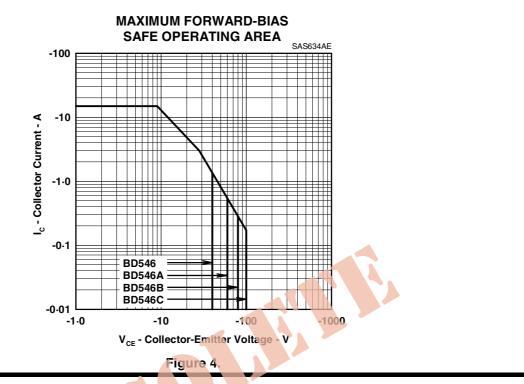


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# BOURNS®

### MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

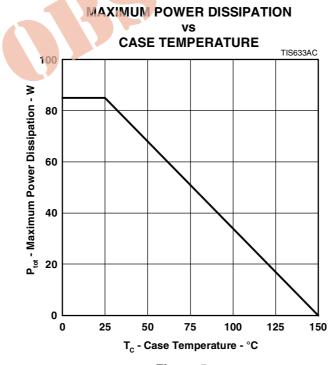


Figure 5.

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